NSN 5961-01-006-9442

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View Online at https://aerobasegroup.com/nsn/5961-01-006-9442 **Inclosure Material:** Metal **Overall Length:** 1.573 inches **Overall Height:** Between 0.250 inches and 0.450 inches Overall Width: 1.050 inches **Mounting Facility Quantity: Internal Configuration:** Junction contact Joint Electronic Device Engineering Council/jedec/case Outline Designation: **Electrode Internally-electrically Connected To Case: Internal Junction Configuration:** Npn **Mounting Method:** Unthreaded hole **Features Provided:** Hermetically sealed case **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 300.0 breakdown voltage, collector-to-base, emitter open and 6.0 emitter to base voltage, static, collector open and 225.0 breakdown voltage, collector-to-emitter, base open **Current Rating Per Characteristic:** 10.00 amperes source cutoff current and 10.00 amperes source cutoff current **Power Rating Per Characteristic:** 100.0 watts small-signal input power, common-collector **Transfer Ratio:** 50.0 static forward current transfer ratio, common-emitter **Maximum Operating Tempurature Per Measurement Point:** 200.0 degrees celsius junction **Terminal Type And Quantity:** 2 pin and 1 case Shelf Life: N/a

No

Unit Of Measure:

Demilitarization:

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